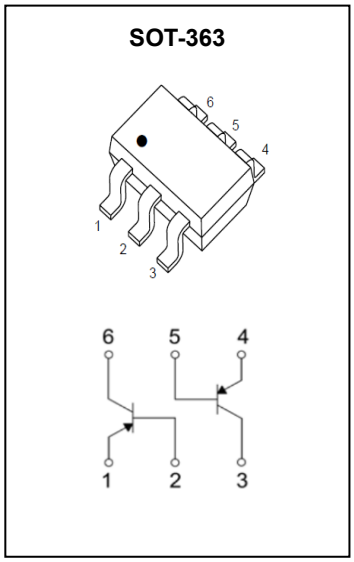
MMDT5401 Dual Transistor(PNP+PNP)



Feature

- Epitaxial planar die construction
- Ideal for low power amplification and switching

Marking: K4M

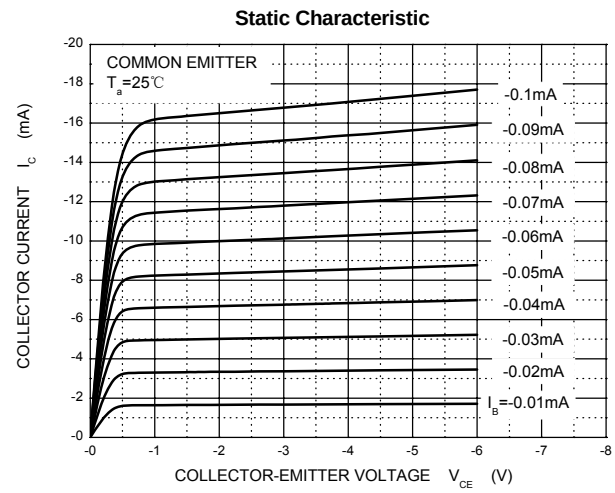
MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

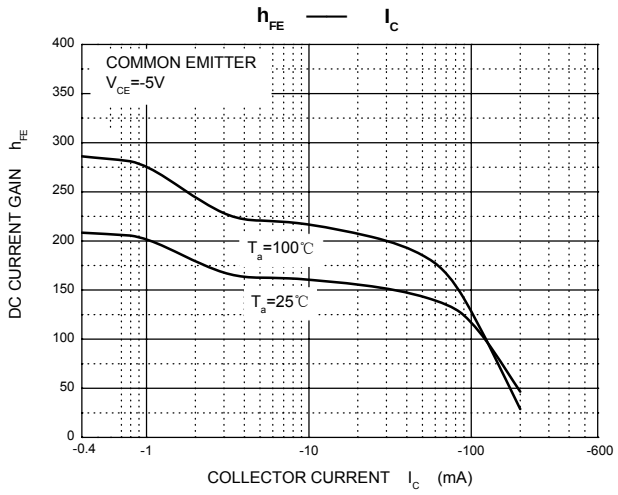
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-160	V
Collector-Emitter Voltage	V_{CEO}	-150	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-0.2	A
Power Dissipation	P_d	0.2	W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~ +150	℃

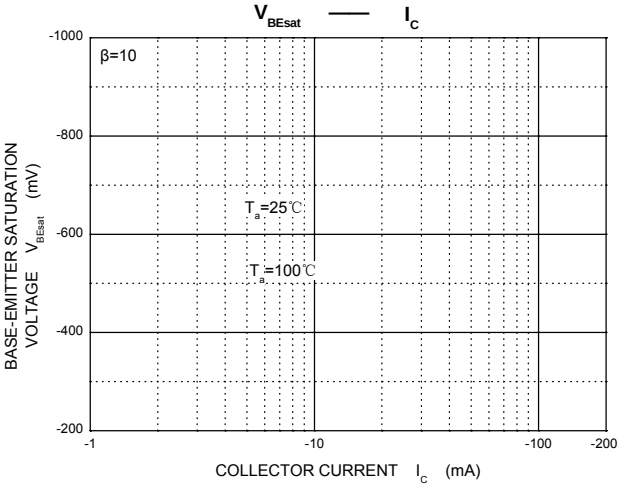
ELECTRICAL CHARACTERISTICS(T_a=25℃ unless otherwise noted)

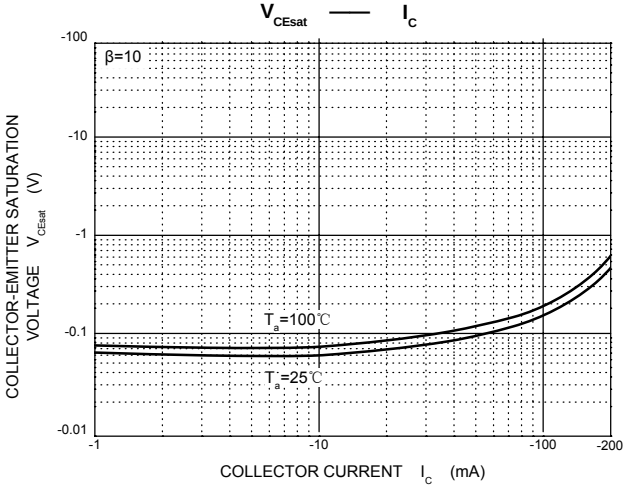
Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA ,I_E=0	-160		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA , I_B=0	-150		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10μA,I_C=0	-5		V
Baes cut-off current	I_{CBO}	V_{CB}=-120V, I_E=0V		-50	nA
Emitter cut-off current	I_{EBO}	V_{EB}=-3V, I_C=0		-50	nA
DC current gain	h_{FE}	V_{CE}=-5V, I_C=-1mA	50		
		V_{CE}=-5V, I_C=-10mA	100	300	
		V_{CE}=-5V, I_C=-50mA	50		
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-10mA, I_B=-1mA		-0.2	V
		I_C=-50mA, I_B=-5mA		-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-10mA, I_B=-1mA		-1	V
		I_C=-50mA, I_B=-5mA		-1	V
Transition frequency	f_T	V_{CE}= -10V, I_C=-10mA,f=100MHz	100		MHZ
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz		6	pF
Noise figure	NF	V_{CE}=-5V,Ic=0.2mA, f=1kHz,R_S=10Ω		8	dB

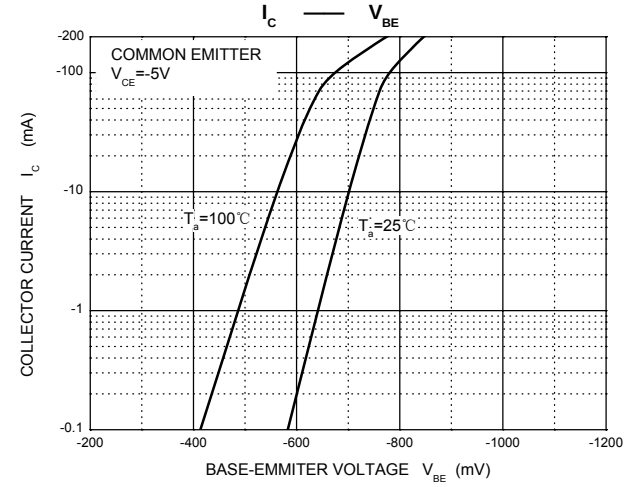
Typical Characteristics

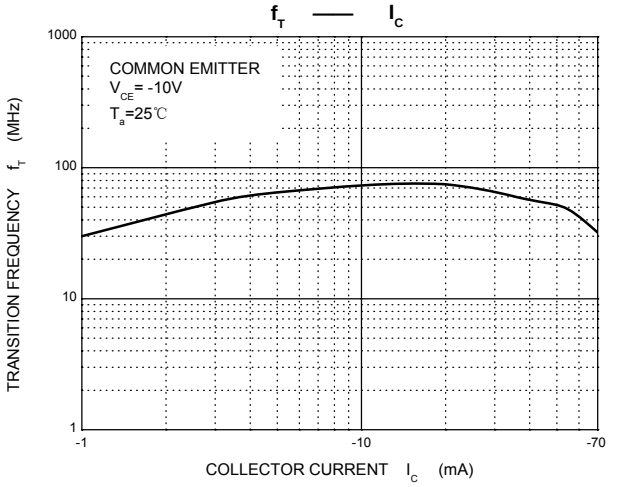




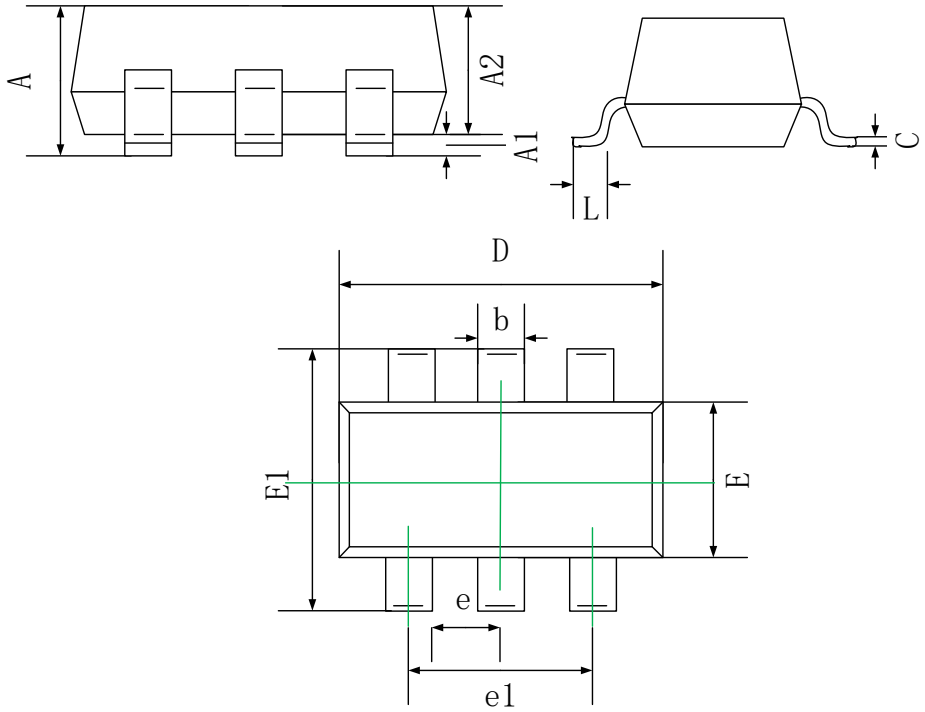






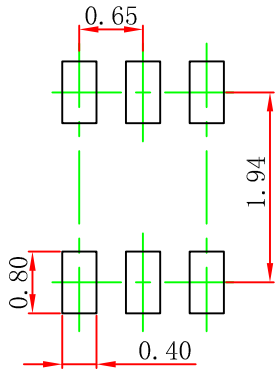


SOT-363 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.10
A1	0.00	0.10
A2	0.90	1.00
b	0.15	0.35
c	0.10	0.15
D	2.00	2.20
E	1.15	1.35
E1	2.15	2.40
e	0.65 REF.	
e1	1.20	1.40
L	0.525 REF.	
L1	0.26	0.46

SOT-363 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.